

BRITISH STANDARDS INSTITUTION

2 PARK STREET, LONDON. W1A 2BS

BS CECC 90102 - 009

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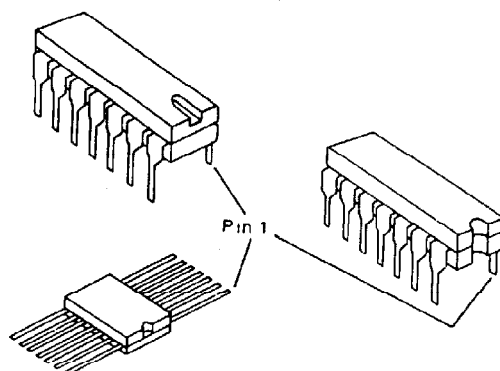
ELECTRONIC COMPONENTS OF ASSESSED QUALITY
DETAIL SPECIFICATION IN ACCORDANCE WITH:

BS CECC 90 000 : 1976
 BS CECC 90 100 : 1977

MANUFACTURERS TYPE NUMBER

54S40
 64S40
 74S40
 84S40

Outline not to scale: Isometric projection
Marking information see clause 1



Refer to IEC 191-1-50a (type A50B)
 Dual-in-Line (plastic or ceramic)
 refer to Appendix A1.3
 Flatpack (metal or ceramic)

SEE PD 9002 AND CECC 00 200
 For ordering information see
 clause 1

**DUAL 4-INPUT POSITIVE
 NAND BUFFERS**

TYPICAL CONSTRUCTION
 SILICON MONOLITHIC BIPOLAR
 CAVITY AND NON-CAVITY
 PACKAGES

ASSESSMENT LEVELS
 R, S, T, AND V

1. Type description

1.1 Truth table

INPUTS				OUTPUT
A	B	C	D	Y
L	X	X	X	H
X	L	X	X	H
X	X	L	X	H
X	X	X	L	H
H	H	H	H	L

H = High level

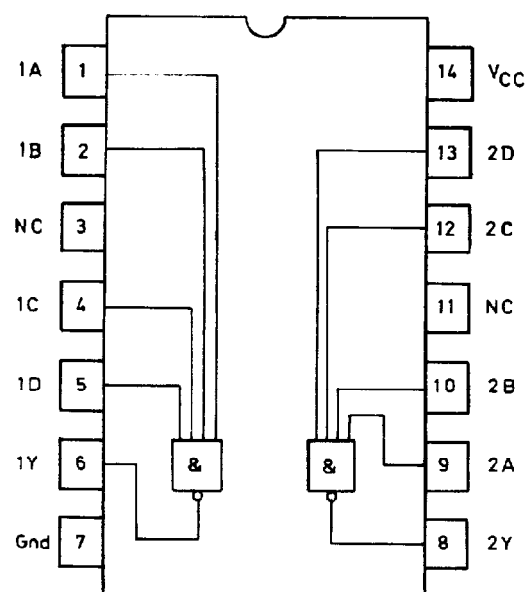
L = Low level

X = Logic level irrelevant

Refer to Qualified Products List PD 9002 and/or CECC 00 200
 for details of manufacturers approved to this specification

1.2 Terminal identification, type designation and marking

1.2.1 Terminal identificaiton



Dual 4-input positive Nand buffers

Terminals marked with NC are not connected internally and may be used as electrical support points. The applied voltage shall not exceed 7,0V.

1.2.2 Type designation

TEMPERATURE RANGE	PACKAGE		
	Ceramic Dual-in-Line	Plastic Dual-in-Line	Ceramic Flatpack
0 + 70	74S40J	N	W
-25 + 85	84S40J		
-40 + 85	64S40J		
-55 +125	54S40J		

1.2.3 Marking

Each integrated circuit shall bear the following markings:

- (1) Terminal identification
- (2) Type designation
- (3) Date code
- (4) Factory identification code (unless derived from trademark)
- (5) Manufacturers trade name or mark
- (6) Mark of conformity (unless a certificate of conformity is used)

1.3 Ordering information

Orders for these integrated circuits shall contain the following minimum information:

Manufacturers integrated circuit type designation, screening procedures and assessment levels as detailed to this CECC specification number.

(For details of screening procedures see Appendix A1.1).

2. Limiting conditions of use (not for inspection purposes)

2.1	Minimum and maximum continuous supply voltage	V_{CC}						-0,5V +7,0V
2.2	Minimum and maximum input voltages							
2.2.1	Minimum and maximum input voltage	V_I						-0,5V +5,5V
2.2.2	Maximum input voltage between multiple emitter transistor inputs	V_{II}						+5,5V
2.3	Minimum and maximum operating ambient temperatures	$T_{amb}(^{\circ}C)$	min.	max.	54S	64S	74S	84S
					-55	-40	0	-25
					+125	+85	+70	+85
2.4	Minimum and maximum storage temperatures	$T_{stg}(^{\circ}C)$	min.	max.	-65	(All types)		
					+150			

3. Recommended operating conditions and associated characteristics (not for inspection purposes)

3.1 Recommended operating conditions

These apply over the operating ambient temperature range unless otherwise stated.

3.1 (contd)

Description	Symbol	Type	Value	Unit
Positive supply voltage range	V_{CC}	54S 64/74/84S	4,5 - 5,5 4,75 - 5,25	V V
Minimum value of High level input voltage	V_{IHB}	All types	2,0	V
Maximum value of High level input voltage	V_{IHA}	All types	5,5	V
Minimum value of Low level input voltage	V_{ILB}	All types	0	V
Maximum value of Low level input voltage	V_{ILA}	All types	0,8	V
Maximum value of Low level output current for each output	I_{OLA}	All types	60,0	mA
Maximum value of output current for each output at V_{OH}	$-I_{OHA}$	All types	3,0	mA
D.C. noise margin				
at Low level ($V_{ILA} - V_{OLA}$)	V_{NL}	All types	0,3	V
at High level ($V_{OHB} - V_{IHB}$)	V_{NH}	54S 64/74/84S	0,5 0,7	V V

3.2 Associated characteristics

- 3.2.1 Minimum and maximum values are given for the worst case operation over the ambient temperature range, except for those conditions marked with an asterisk (*)

	54S	64S	74S	84S	
T _{amb} min.	-55	-40	0	-25	°C
T _{amb} max.	+125	+85	+70	+85	
V _{CC} min.	4,5	4,75			V
V _{CC} max.	5,5	5,25			

3.2.2

Characteristics	Conditions	$V_{CC}(V)$	Symbol	Min.	Max.	Unit
Total supply current at High level	$V_{IN}^{(1)}$ to give High level output	$V_{CC} \text{ max.}$	I_{CCH}	-	18,0	mA
Total supply current at Low level	$V_{IN}^{(1)}$ to give Low level output	$V_{CC} \text{ max.}$	I_{CCL}	-	44,0	mA
High level input current	$V_{IH(1)} = 5,5V$ $V_{IH(2)} = 2,7V$	$V_{CC} \text{ max.}$	$I_{IH(1)}$	-	1,0	mA
		$V_{CC} \text{ max.}$	$I_{IH(2)}$	-	100,0	μA
Low level input current	$V_{IN} = 0,5V$	$V_{CC} \text{ max.}$	$-I_{IL}$	-	4,0	mA
Input clamping voltage	$-I_{IC} = 18,0mA$	$V_{CC} \text{ min.}$	$-V_{IC}$	-	1,2	V
Output voltage 54S 64/74/84S All types	$I_{OH} = 3,0mA$ $I_{OH} = 3,0mA$ $I_{OL} = 60,0mA^{(2)}$	$V_{CC} \text{ min.}$	V_{OH}	2,5	-	V
			V_{OH}	2,7	-	V
			V_{OL}	-	0,5	V
Output short circuit current	V_{IN} to give High level output $V_O = 0V^{(3)}$	$V_{CC} \text{ max.}$	$-I_{OS}$	50,0	225,0	mA
Propagation times All types	$T_{amb} = 25^\circ C^*$ test conditions as in Sub-group A5	5,0V				
High to Low level			t_{PHL}	-	6,5	ns
Low to High level			t_{PLH}	-	6,5	ns

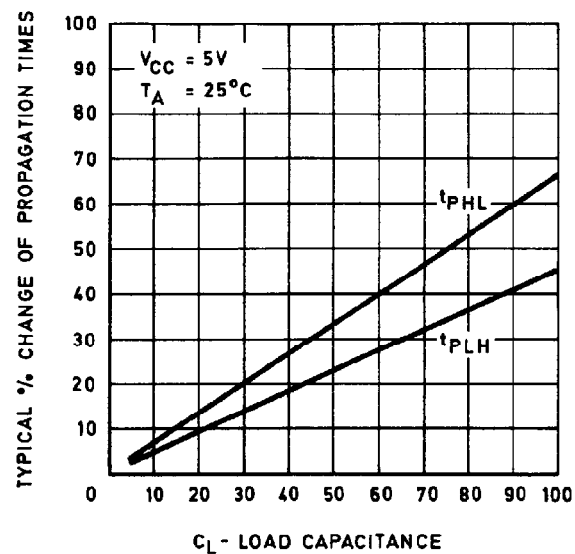
(1) To all inputs, (2) Fan out = 30,

(3) Only one output at a time, duration $t \leq 1 \text{ sec}$

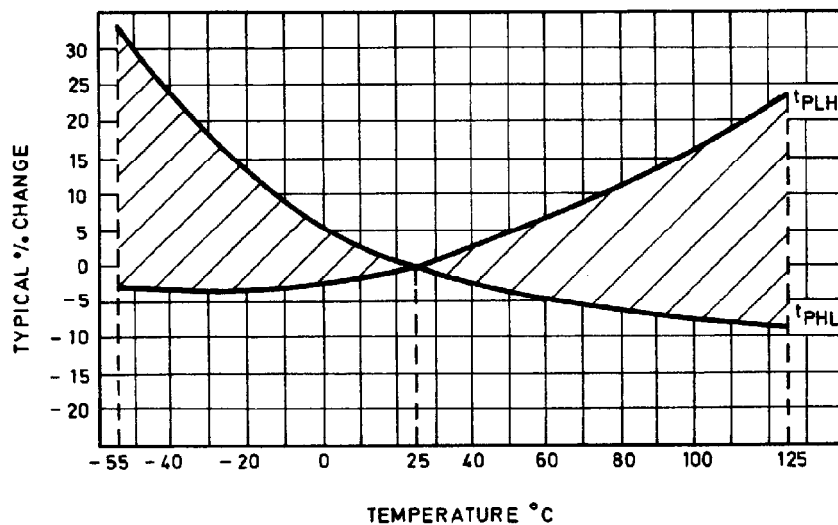
*See clauses 3.1 and 3.2.1 of this specification

3.3 Supplementary information

3.3.1 Change of typical propagation time with output loading



3.3.2 Variation of propagation time with temperature



3.3.3 Gates

Inputs of unused gates should be connected in such a way that the output is set to High level to ensure minimum power dissipation.

For Nand gates unused inputs shall be maintained at a positive voltage $> 2,5V$ (54S) or $2,7V$ (64/74/84S) but shall not exceed the absolute maximum rating of $5,5V$.